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March 20, 2003

VIA FACSIMILE

To: Examiner Renzo Rocchegiani
Group Art Unit No. 2825
U.S.P.T.O.

Facsimile No.: (703) 872-9318

From: Sean M. McGinn

Facsimile No.: (703) 761-2375

Re: Enclosed Supplemental Amendment
U.S. Patent Application Serial No. 09/817,120
Our Reference: YOR.213

Dear Examiner Rocchegiani:

Further to the Amendment filed on March 4, 2003, enclosed is a Supplemental Amendment, which should place the above-referenced case in condition for allowance.

Thank you in advance for your kind consideration on this case.

Very truly yours,



Sean M. McGinn

SMM:abs
Enclosure

Total No. of Pages Transmitted: 13

#12 / Suppl
Amend B
9 Total
3/25/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chan et al.

Serial No.: 09/817,120

Group Art Unit: 2825

Filed: March 27, 2001

Examiner: R. Rocchegiani

For: METHOD FOR MANUFACTURING DEVICE SUBSTRATE WITH METAL
BACK-GATE AND STRUCTURE FORMED THEREBY

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Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

MAR 20 2003

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SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

Further to the Amendment filed on March 4, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please add the following new claims:

- C1
- B1
- 39. The method of claim 1, wherein said providing said intermediate gluing layer on said passivation layer comprises growing said intermediate layer by in-situ ultra high vacuum chemical vapor deposition (UHV CVD) growth of metal-Si-N.
40. The method of claim 39, wherein said metal comprises tungsten.
41. The method of claim 18, wherein said providing said passivation layer comprises growing said passivation layer by in-situ ultra high vacuum chemical vapor deposition (UHV CVD) growth of metal-Si-N.
42. The method of claim 41, wherein said metal comprises tungsten.